

B	2018-8				
C	2021-10-26	4			

, /21.A<.3= /&

SOT-363 PNP

Double silicon PNP transistor in a SOT-363 Plastic Package

& * & 7 , : <B1, / &

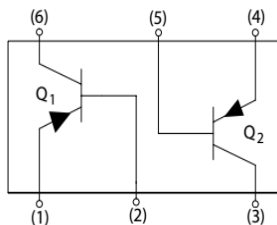
600mA

Collector currents to 600mA. HF Product.

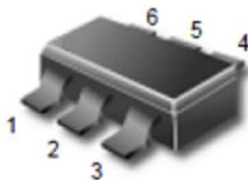
& * & %AA9.2 : <.3= / & &

General purpose amplifier.

& * &) CB. - : 9 , =<8.12B.<&



& * & D.==.@&



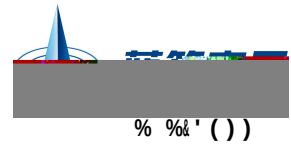
PIN 1 4 Emitter

PIN 2 5 Base

PIN 3 6 Collector

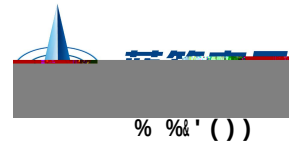
& * & 67)&89: / / .; .2 : <.3= / & > & : 1? .=@&

See Marking Instructions

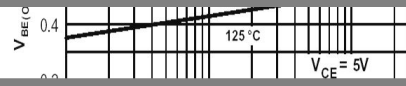


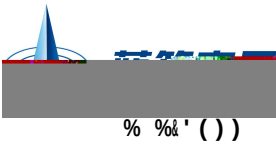
&

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	



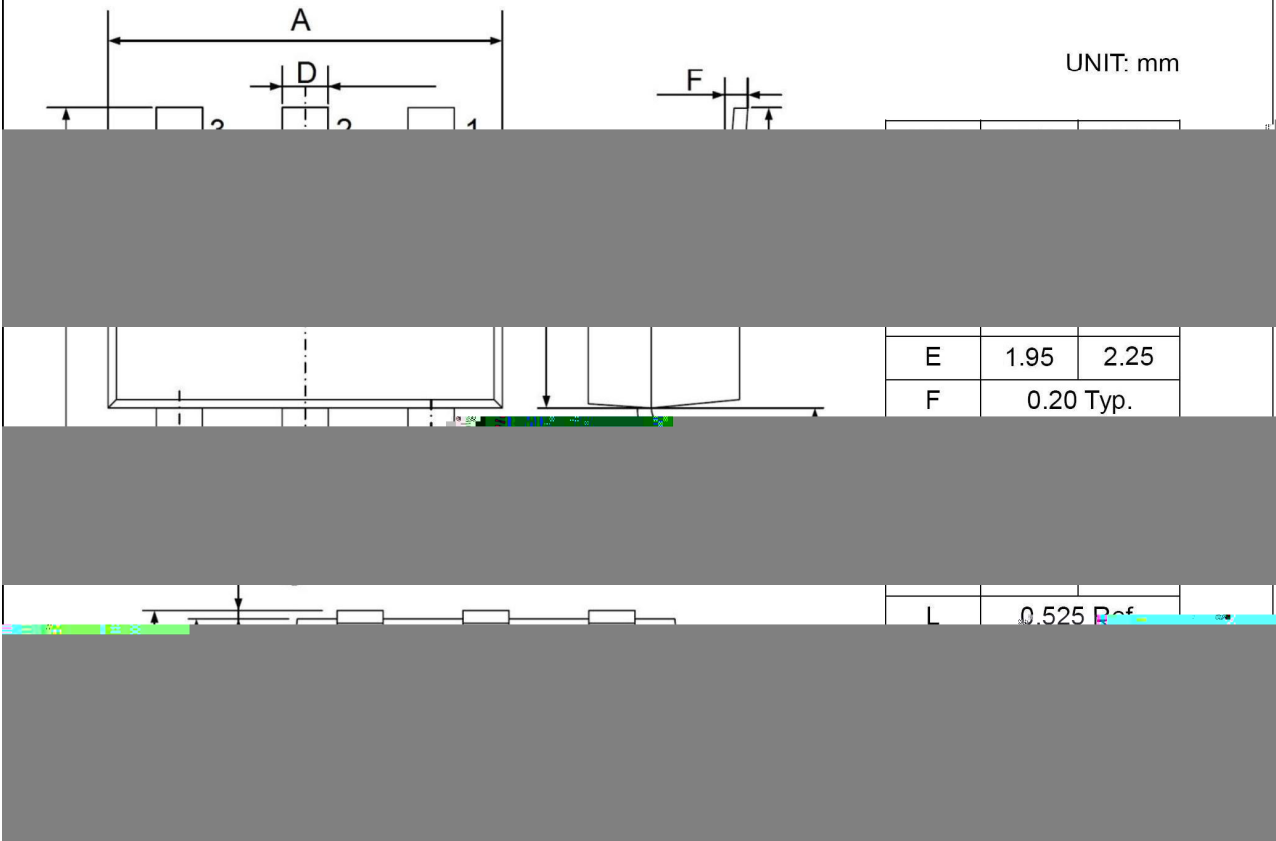
& & * & &) 9, 2<1.2:9&86:1:2<, 1./<.2&8B1- , &

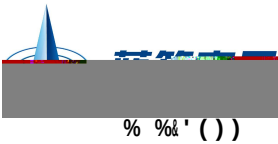




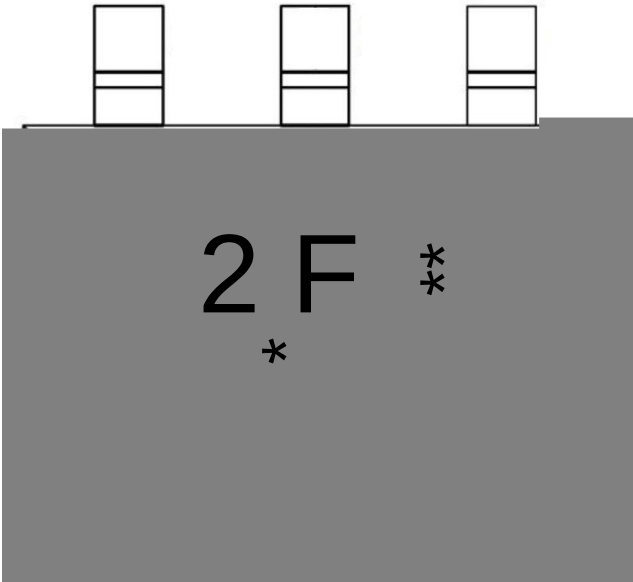
&& *&& D:2?:@,& .G,=/ .3=/&

SOT-363-6L





& & * & & : 1 ? . = @ & N = / < 1 B 2 < . 3 = / &



● “ 1 ”

2F

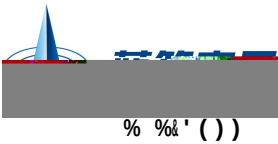
***:

Note:

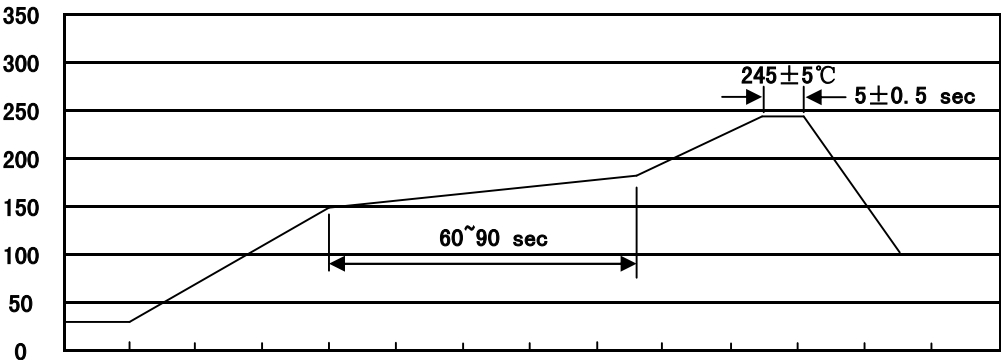
● “1” Pin

2F Product Type Code

***: Lot No. Code, code change with Lot No.



H K& *& & Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | |
|---|-------------|-----------|--|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | 2 10°C/sec. | | 3. Cooling Speed: 2~10°C/sec. |

& *& & + , / . / < : = 2 , < 3 & ' 3 9 0 , 1 . = @ & (, : < & , / < & 8 3 = 0 . < . 3 = / &

260±5°C 10±1 sec. Temp.:260±5°C Time:10±1 sec

& *& & D : 2 ? : @ . = @ & ' D) 8 0 &

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-363	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

& *& & P3<.2 , / &